

TOSHIBA PHOTOINTERRUPTER INFRARED LED + PHOTOTRANSISTOR

TLP831

HOME ELECTRONICS EQUIPMENT SUCH AS VCRS AND CD PLAYERS

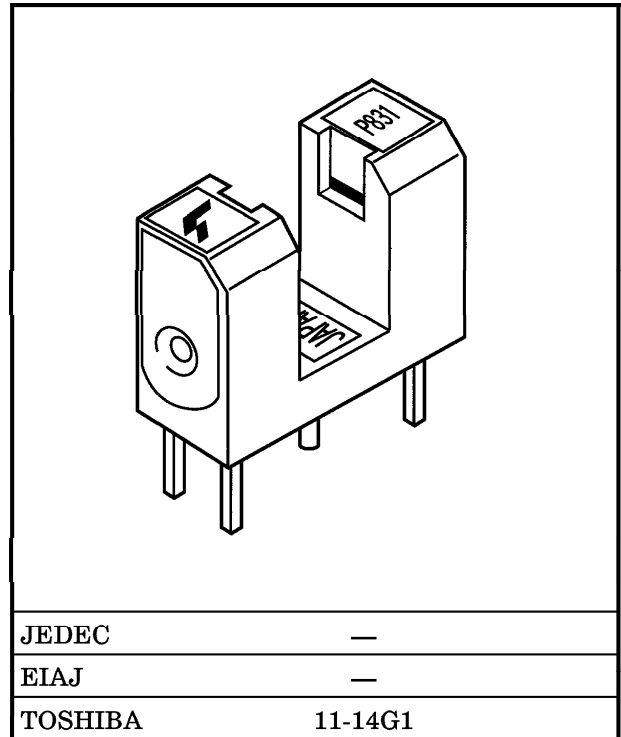
OA EQUIPMENT SUCH AS COPIERS, PRINTERS, AND FACSIMILES

AUTOMATIC SERVICING EQUIPMENT SUCH AS COMMODITY AND TICKET VENDING MACHINES

VARIOUS POSITION DETECTION SENSOR

The TLP831 photointerrupter consists of a high radiant power GaAs infrared LED and a Si phototransistor.

Housed in a short lead package, this device is ideal for automatic mounting.



Weight : 0.58g (Typ.)

- Printed wiring board direct mounting type
(with a locating pin)
- Short lead type enabling automatic mounting
: Lead length $3.4 \pm 0.3\text{mm}$
- Board thickness : 1.6mm or less
- Gap : 4.2mm
- Resolution : Slit width 0.5mm
- High current transfer ratio
: $I_C / I_F = 5\%$ (min)
- High response speed
: $t_r, t_f = 15\mu\text{s}$ (typ.)
- Detector side is of visible light cut type.
- Material of the package
: Polybutylene terephthalate (UL94V-0, Black color)

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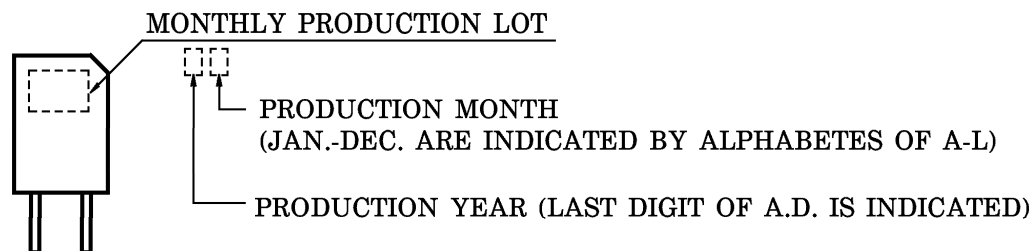
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I _F	50	mA
	Forward Current Derating (Ta > 25°C)	ΔI _F /°C	-0.33	mA/°C
	Reverse Voltage	V _R	5	V
DETECTOR	Collector-Emitter Voltage	V _{CEO}	35	V
	Emitter-Collector Voltage	V _{ECO}	5	V
	Collector Power Dissipation	P _C	75	mW
	Collector Power Dissipation Derating (Ta > 25°C)	ΔP _C /°C	-1	mW/°C
	Collector Current	I _C	50	mA
Operating Temperature		T _{opr}	-30~85	°C
Storage Temperature		T _{stg}	-40~100	°C
Soldering Temperature (5s)(Note 1)		T _{sol}	260	°C

Note 1 : At the location of 1.5mm from the resin package bottom

PRODUCT INDICATION



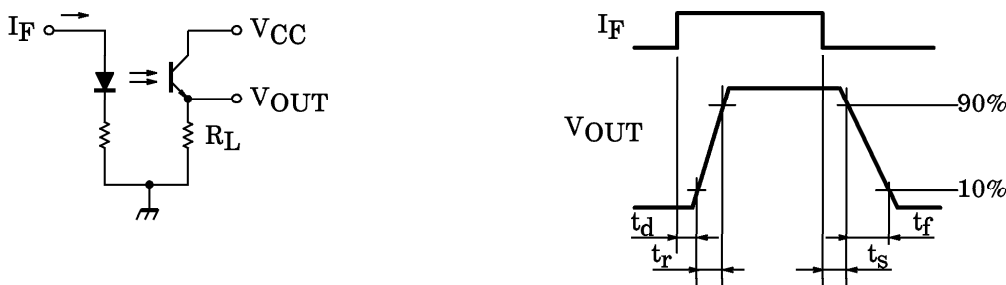
RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{CC}	—	5	24	V
Forward Current	I _F	—	—	25	mA
Operating Temperature	T _{opr}	-10	—	75	°C

OPTO ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.00	1.15	1.30	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Peak Emission Wavelength	λ_P	$I_F = 10\text{mA}$	—	940	—	nm
DETECTOR	Dark Current	$I_D (I_{CEO})$	$V_{CE} = 24\text{V}, I_F = 0$	—	—	0.1	μA
	Peak Sensitivity Wavelength	λ_P		—	870	—	nm
COUPLED	Current Transfer Ratio	I_C / I_F	$V_{CE} = 2\text{V}, I_F = 10\text{mA}$	5	—	100	%
	Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_F = 20\text{mA}, I_C = 0.5\text{mA}$	—	0.1	0.35	V
	Rise Time	t_r	$V_{CC} = 5\text{V}, I_C = 1\text{mA}$	—	15	50	μs
	Fall Time	t_f	$R_L = 1\text{k}\Omega$ (Note 2)	—	15	50	

Note 2 : Switching time measurement circuit and waveform



PRECAUTIONS

- When removing flux with chemicals after soldering, clean only the leads on the soldering side; do not dip the whole package for cleaning.
Chemicals remaining on a surface of LED or phototransistor, if any, would have a bad influence to the optical characteristics and it may severely lower the conversion efficiency.
- The environment to install the device should be determined carefully. Oil or chemicals may cause the package to be dissolved or cracked.
- The device should be mounted on an unwarped surface.
- Install this device as avoiding the disturbance light as possible. A visible light cut-off type phototransistor which blocks light with frequencies of 700nm or above is used. However, the device cannot block infrared light with a wavelength of 700nm or more, and it may do mistaken movements.
- The current transfer ratio is gradually lowered when infrared LED is powered. The efficiency deterioration by aging should be considered when designing the circuit.

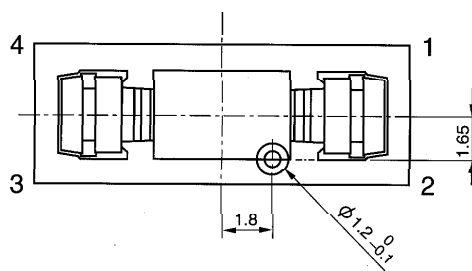
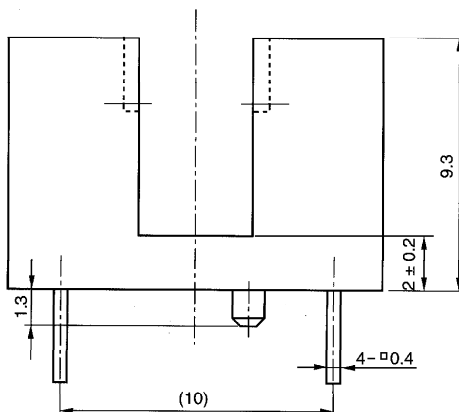
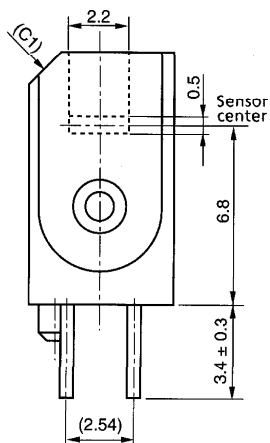
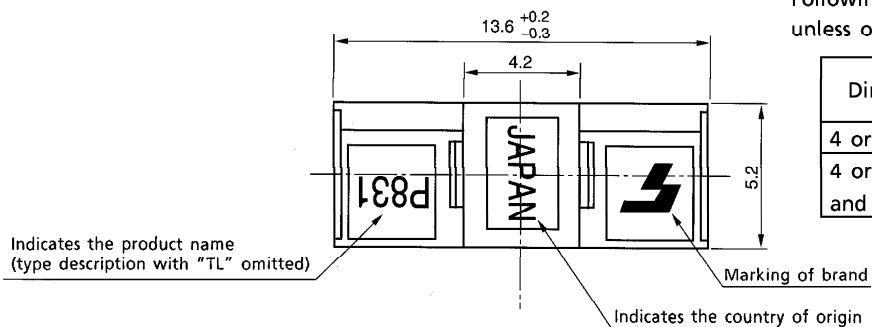
OUTLINE : TOSHIBA

Unit : mm

() : REFERENCE VALUE

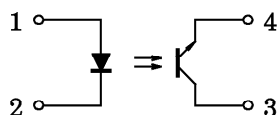
Following table shows differences unless otherwise specified

Dimensions	Tolerant Differences
4 or less	± 0.1
4 or more and 18 or less	± 0.2



Weight : 0.58g (Typ.)

PIN CONNECTION



1. ANODE
2. CATHODE
3. COLLECTOR
4. EMITTER

